

MOSFET – P-Channel, POWERTRENCH®

-30 V, -4.9 A, 42 mΩ

FDC610PZ

General Description

This P-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance. These devices are well suited for battery power applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

- Max $r_{DS(on)}$ = 42 mΩ at $V_{GS} = -10$ V, $I_D = -4.9$ A
- Max $r_{DS(on)}$ = 75 mΩ at $V_{GS} = -4.5$ V, $I_D = -3.7$ A
- Low Gate Charge (17 nC typical)
- High Performance Trench Technology for Extremely Low $r_{DS(on)}$
- SUPERSOT™-6 Package: Small Footprint (72% smaller than Standard SO-8) Low Profile (1 mm thick)
- This Device is Pb-Free, Halide Free and is RoHS Compliant

Application

- DC-DC Conversion

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

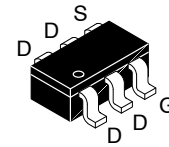
| Symbol | Parameter | Ratings | Units |
|----------------|--|----------------------|------------------|
| V_{DS} | Drain to Source Voltage | -30 | V |
| V_{GS} | Gate to Source Voltage | ± 25 | V |
| I_D | Drain Current | Continuous (Note 1a) | -4.9 A |
| | | Pulsed | |
| P_D | Power Dissipation | (Note 1a) | 1.6 W |
| | | (Note 1b) | 0.8 |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

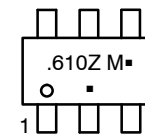
| Symbol | Parameter | Ratings | Units |
|-----------------|---|---------|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 78 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1b) | 156 | $^\circ\text{C/W}$ |

| V_{DS} | $r_{DS(on)}$ MAX | I_D MAX |
|----------|------------------|-----------|
| -30 V | 42 mΩ @ -10 V | -4.9 A |
| | 75 mΩ @ -4.5 V | -3.7 A |



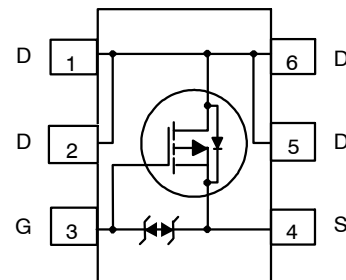
TSOT23 6-Lead
SUPERSOT™-6
CASE 419BL

MARKING DIAGRAM



.610Z = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

PINOUT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

OFF CHARACTERISTICS

| | | | | | | |
|--------------------------------------|---|---|-----|-----|-----|-------|
| BV _{DSS} | Drain to Source Breakdown Voltage | I _D = -250 μA, V _{GS} = 0 V | -30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | I _D = -250 μA, referenced to 25°C | | -22 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = -24 V, V _{GS} = 0 V | | | -1 | μA |
| I _{GSS} | Gate to Source Leakage Current | V _{GS} = ±25 V, V _{DS} = 0 V | | | ±10 | μA |

ON CHARACTERISTICS

| | | | | | | |
|--|--|--|----|------|----|-------|
| V _{GS(th)} | Gate to Source Threshold Voltage | V _{GS} = V _{DS} , I _D = -250 μA | -1 | -2.2 | -3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | I _D = -250 μA, referenced to 25°C | | -6 | | mV/°C |
| r _{DS(on)} | Static Drain to Source On Resistance | V _{GS} = -10 V, I _D = -4.9 A | | 36 | 42 | mΩ |
| | | V _{GS} = -4.5 V, I _D = -3.7 A | | 58 | 75 | |
| | | V _{GS} = -10 V, I _D = -4.9 A, T _J = 125°C | | 50 | 60 | |
| g _{FS} | Forward Transconductance | V _{DD} = -10 V, I _D = -4.9 A | | 15 | | S |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|------------------|------------------------------|---|--|-----|------|----|
| C _{iss} | Input Capacitance | V _{DS} = -15 V, V _{GS} = 0 V, f = 1 MHz | | 755 | 1005 | pF |
| C _{oss} | Output Capacitance | | | 145 | 195 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 125 | 190 | pF |
| R _g | Gate Resistance | f = 1 MHz | | 13 | | Ω |

SWITCHING CHARACTERISTICS

| | | | | | | |
|---------------------|-------------------------------|--|--|-----|----|----|
| t _{d(on)} | Turn-On Delay Time | V _{DD} = -15 V, I _D = -4.9 A, V _{GS} = -10 V, R _{GEN} = 6 Ω | | 7 | 14 | ns |
| t _r | Rise Time | | | 4 | 10 | ns |
| t _{d(off)} | Turn-Off Delay Time | | | 33 | 53 | ns |
| t _f | Fall Time | | | 23 | 37 | ns |
| Q _g | Total Gate Charge | V _{GS} = 0 V to -10 V, V _{DD} = -15 V, I _D = -4.9 A | | 17 | 24 | nC |
| | | V _{GS} = 0 V to -4.5 V, V _{DD} = -15 V, I _D = -4.9 A | | 9 | 13 | nC |
| Q _{gs} | Gate to Source Gate Charge | V _{DD} = -15 V, I _D = -4.9 A | | 2.9 | | nC |
| Q _{gd} | Gate to Drain "Miller" Charge | | | 4.3 | | nC |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | |
|-----------------|---|---|--|------|------|----|
| I _S | Maximum Continuous Drain–Source Diode Forward Current | | | | –1.3 | A |
| V _{SD} | Source to Drain Diode Forward Voltage | V _{GS} = 0 V, I _S = –1.3 A (Note 2) | | –0.8 | –1.2 | V |
| t _{rr} | Reverse Recovery Time | I _F = –4.9 A, di/dt = 100 A/μs | | 19 | 35 | ns |
| Q _{rr} | Reverse Recovery Charge | | | 9 | 18 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. R_{θJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.



a. 78°C/W when mounted on a 1 in² pad of 2 oz. copper



b. 156°C/W when mounted on a minimum pad of 2 oz. copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

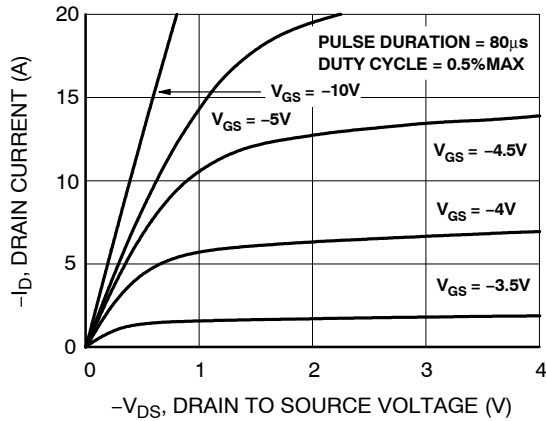


Figure 1. On-Region Characteristics

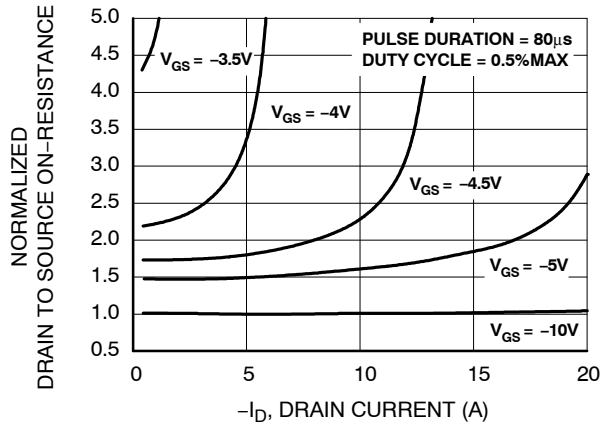


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

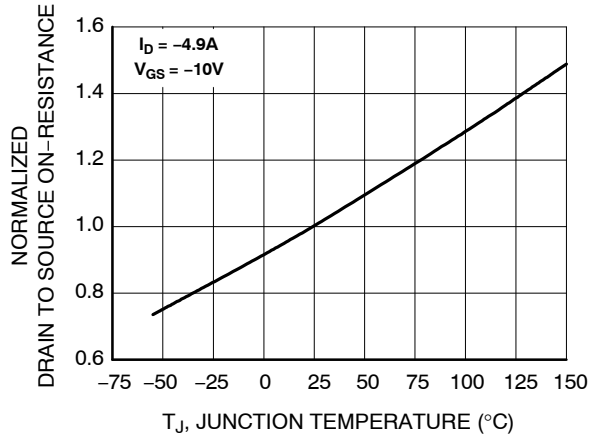


Figure 3. Normalized On-Resistance vs Junction Temperature

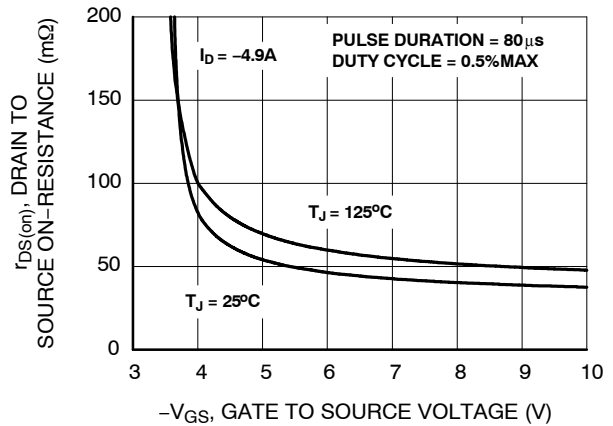


Figure 4. On-Resistance vs Gate to Source Voltage

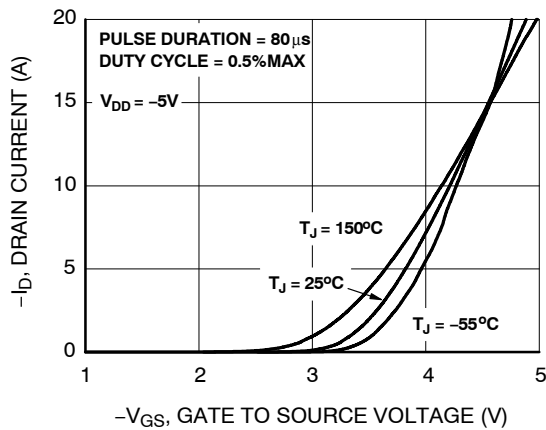


Figure 5. Transfer Characteristics

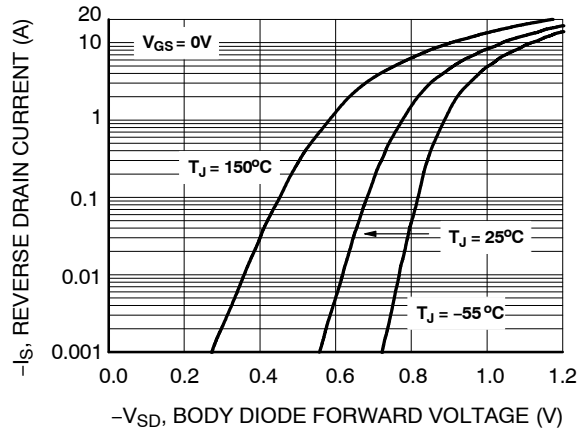


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

FDC610PZ

TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

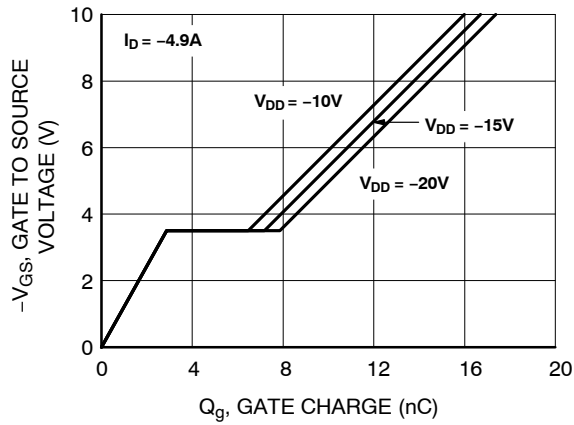


Figure 7. Gate Charge Characteristics

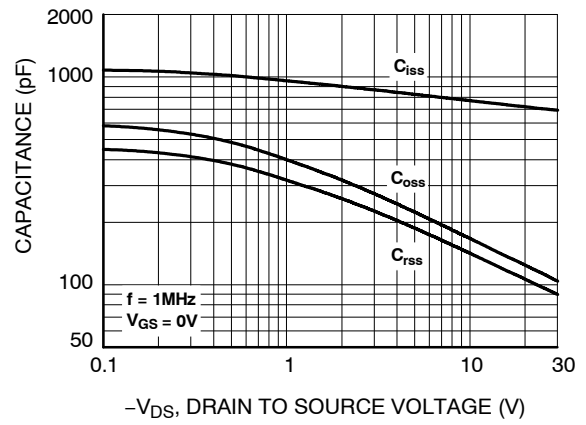


Figure 8. Capacitance vs Drain to Source Voltage

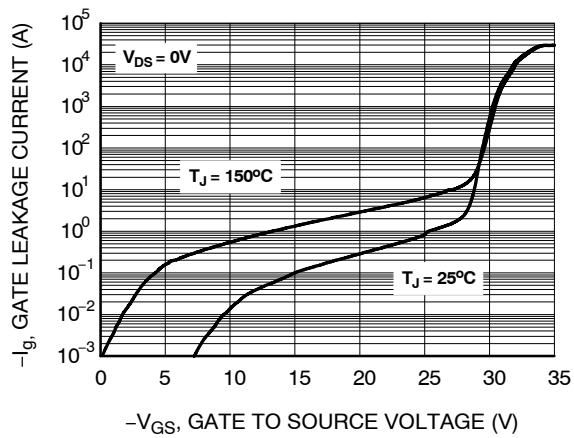


Figure 9. Gate Leakage Current vs. Gate to Source Voltage

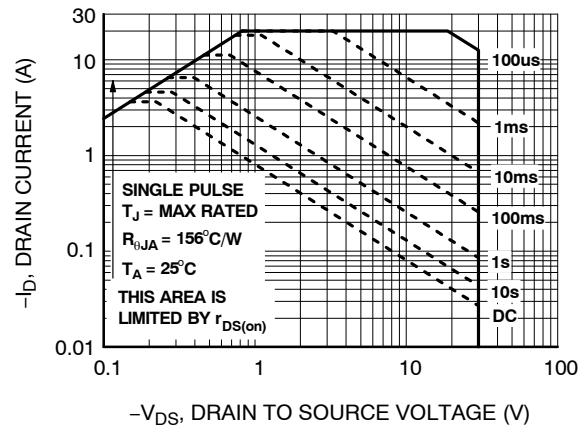


Figure 10. Forward Bias Safe Operating Area

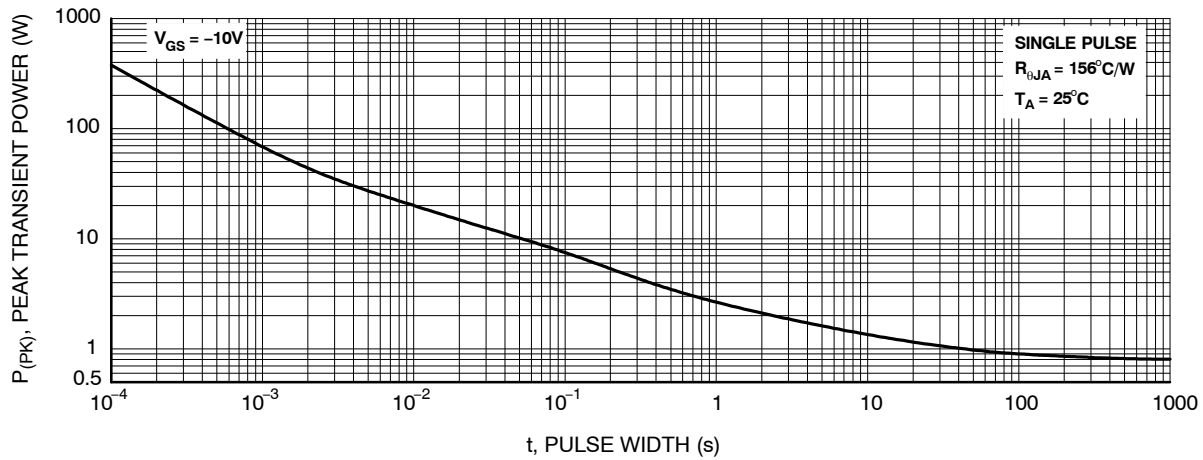


Figure 11. Single Pulse Maximum Power Dissipation

FDC610PZ

TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

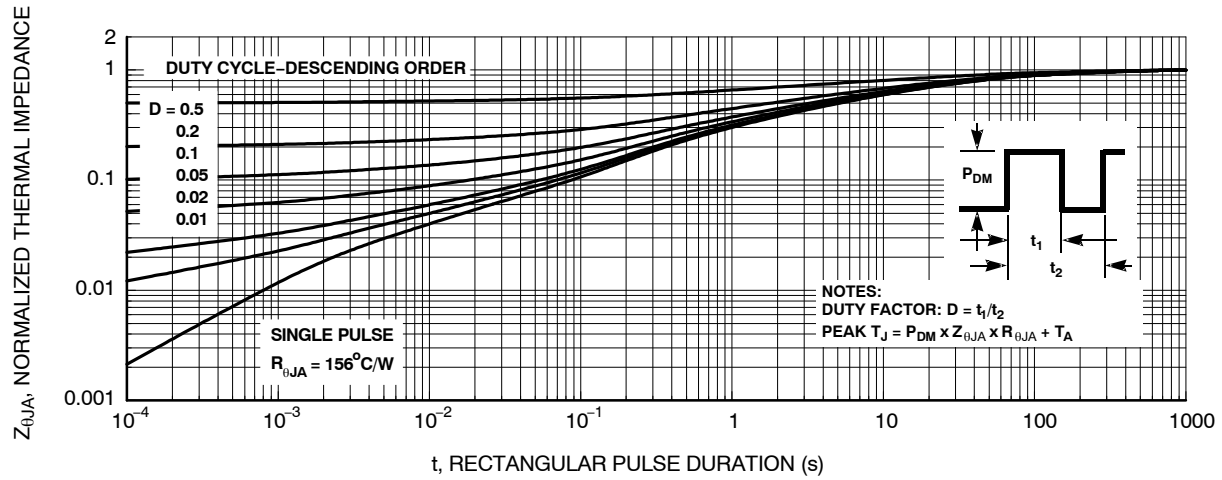


Figure 12. Transient Thermal Response Curve

ORDERING INFORMATION

| Device | Device Marking | Package Type | Shipping [†] |
|----------|----------------|-------------------------------------|-----------------------|
| FDC610PZ | .610Z | TSOT-23-6 (Pb-Free, Halide Free) | 3000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

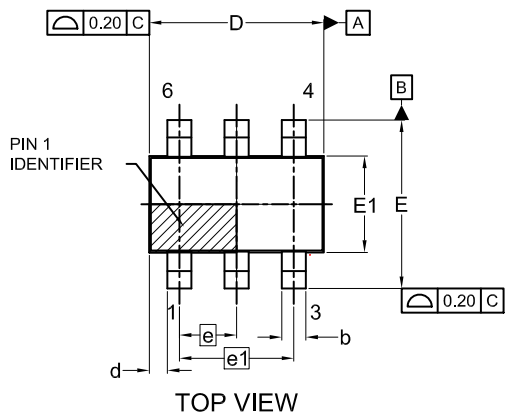
ON Semiconductor®



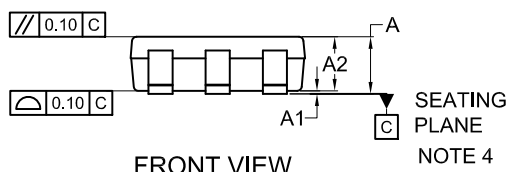
SCALE 2:1

TSOT23 6-Lead CASE 419BL ISSUE A

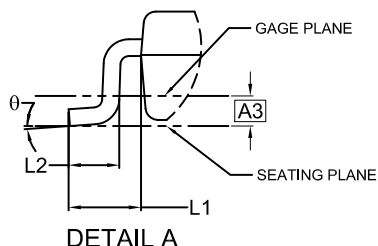
DATE 31 AUG 2020



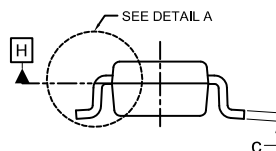
TOP VIEW



FRONT VIEW

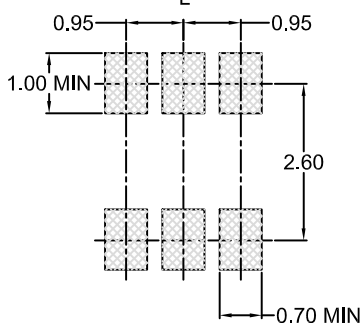


DETAIL A



SIDE VIEW

SYMM
⌀



LAND PATTERN RECOMMENDATION

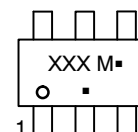
*FOR ADDITIONAL INFORMATION ON OUR
Pb-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE ON SEMICONDUCTOR
SOLDERING AND MOUNTING TECHNIQUES
REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.25MM PER END. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
4. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | 0.05 | 0.10 |
| A2 | 0.70 | 0.85 | 1.00 |
| A3 | 0.25 BSC | | |
| b | 0.25 | 0.38 | 0.50 |
| c | 0.10 | 0.18 | 0.26 |
| D | 2.80 | 2.95 | 3.10 |
| d | 0.30 REF | | |
| E | 2.50 | 2.75 | 3.00 |
| E1 | 1.30 | 1.50 | 1.70 |
| e | 0.95 BSC | | |
| e1 | 1.90 BSC | | |
| L1 | 0.60 REF | | |
| L2 | 0.20 | 0.40 | 0.60 |
| ⌀ | 0° | --- | 10° |

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

| | | |
|------------------|---------------|--|
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| DESCRIPTION: | TSOT23 6-Lead | PAGE 1 OF 1 |

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